

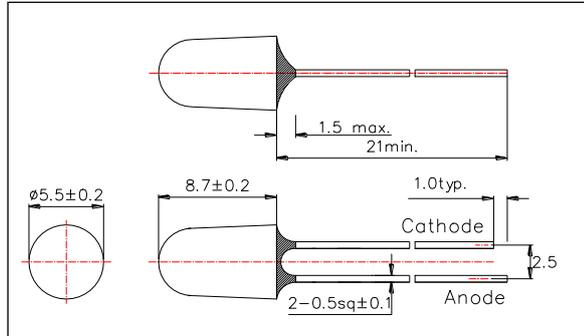
**L850-06-2C**  
Infrared LED Lamp

L850-06-2C is an AlGaAs LED mounted on a lead frame with a clear epoxy lens, which LED is designed for higher radiant intensity of typical 170mW/sr at DC. On forward bias, it emits a spectral band of radiation that peaks at 850nm.

<Specifications>

1. Product Name: Infrared LED Lamp
2. Type Number: L850-06-2C
3. Chip:
  - Chip material: AlGaAs
  - Peak Wavelength: 850nm typ.
4. Package
  - Type: Φ5mm Clear Molding
  - Resin Material: Epoxy Resin
  - Lead Frame: Soldered(Lead Free)

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Power Dissipation	PD	155	mW
Forward Current	IF	100	mA
Pulse Forward Current*	IFP	1000	mA
Reverse Voltage	VR	5	V
Operating Temperature	TOPR	-30 ~ +85	°C
Storage Temperature	TSTG	-30 ~ +100	°C
Soldering Temperature**	TSOL	260	°C

\* Duty=1% and Pulse Width=10us.

\*\* Soldering condition must be completed within 3 second at 260 °C.

Electro-Optical Characteristics [Ta=25°C]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=50mA		1.46	1.60	V
Reverse Current	IR	VR=5V			10	uA
Total Radiated Power*	PO	IF=50mA	18	24		mW
Radiant Intensity**	IE	IF=50mA	120	170		mW/sr
		IFP=1000mA		3400		
Peak Wavelength	λP	IF=50mA	840	850	860	nm
Half Width	Δλ	IF=50mA		40		nm
Viewing Half Angle	θ1/2	IF=50mA		±8		deg
Rise Time	tr	IF=50mA		15		ns
Fall Time	tf	IF=50mA		10		ns

\* Measured by Photodyne #500

\*\* Measured by Tektronix J-6512

